

# **isc Silicon NPN Power Transistor**

# BD226/228/230

#### **DESCRIPTION**

- DC Current Gain-
  - : h<sub>FE</sub>= 40(Min)@ I<sub>C</sub>= 0.15A
- Complement to Type BD227/229/231
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

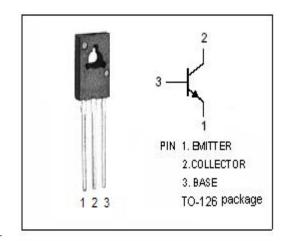
• Designed for use in driver stages in television circuits.

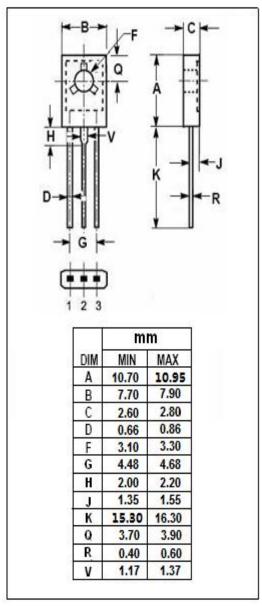
## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT		
	Collector-Base Voltage	BD226	45	V	
V <sub>CBO</sub>		BD228	60		
		BD230	100		
Vceo		BD226	45	V	
	Collector-Emitter Voltage	BD228	60		
		BD230	80		
V <sub>CER</sub>	Collector-Emitter Voltage( $R_{BE}$ = 1k $\Omega$ )	BD226	45	V	
		BD228	60		
		BD230	100		
V <sub>EBO</sub>	Emitter-Base Voltage	5	V		
Ic	Collector Current-Continuo	1.5	Α		
I <sub>CM</sub>	Collector Current-Peak	3.0	Α		
Pc	Collector Power Dissipatio @ T <sub>c</sub> ≤62°C	12.5	W		
TJ	Junction Temperature	150	$^{\circ}\!\mathbb{C}$		
T <sub>stg</sub>	Storage Temperature Ran	-65~150	$^{\circ}$		

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	7	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient		°C/W







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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
Vceo(sus)	Collector-Emitter Sustaining Voltage	BD226		45			
		BD228	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	60			V
		BD230		80			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = 1A; I <sub>B</sub> = 0.1A			0.8	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage		I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V			1.3	V
I <sub>CBO</sub>	Collector Cutoff Current		V <sub>CB</sub> = 30V; I <sub>E</sub> = 0 V <sub>CB</sub> = 30V; I <sub>E</sub> = 0,T <sub>C</sub> =125°C			0.1 10	μА
I <sub>EBO</sub>	Emitter Cutoff Current		V <sub>EB</sub> = 5V; I <sub>C</sub> =0			10	μА
h <sub>FE-1</sub>	DC Current Gain		I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 2V	25			
h <sub>FE-2</sub>	DC Current Gain		I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	25			
h <sub>FE-3</sub>	DC Current Gain		I <sub>C</sub> = 0.15A ; V <sub>CE</sub> = 2V	40		250	
f⊤	Current-Gain—Bandwidth Product		I <sub>C</sub> = 50mA ; V <sub>CE</sub> = 5V		125		MHz

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